Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT404 (D2PAK) surface mountable plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series BT" triac will commutate the full rated RMS current at the maximum rated junction temperature ($T_{i(max)} = 150$ °C) without the aid of a snubber.

2. Features and benefits

- · 3Q technology for improved noise immunity
- High blocking voltage capability
- High junction operating temperature capability (T_{i(max)} = 150 °C)
- · High commutation capability with maximum false trigger immunity
- · High immunity to false turn-on by dV/dt
- Less sensitive gate for very high noise immunity
- Planar passivated for voltage ruggedness and reliability
- · Surface mountable package
- · Triggering in three quadrants only

3. Applications

- Heating controls
- High power motor control
- High power switching
- Applications subject to high temperature (T_{j(max)} = 150 °C)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage			-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 117 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3		-	-	25	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5		-	-	190	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$		-	-	209	Α
T _j	junction temperature			-	-	150	°C
Static characteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$		2	18	50	mA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	2	21	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	2	34	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	31	60	mA
V_{T}	on-state voltage	I _T = 30 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.55	V
Dynamic char	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	-	2300	-	V/µs
		V _{DM} = 536 V; T _j = 125 °C; exponential waveform; gate open circuit	1000	4000	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 25 A; dV_{com}/dt = 20 V/ μ s; (without snubber condition); gate open circuit	-	19	-	A/ms
		V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 25 A; dV_{com}/dt = 20 V/µs; (snubber condition); gate open circuit	_	44	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2		G sym051
3	G	gate	Li	Symoon
mb	T2	mounting base; main terminal 2		
			D2PAK (SOT404)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BTA225B-800BT	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 117 ^{\circ}\text{C}$; Fig. 2; Fig. 3	-	25	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	190	А
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	209	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	180	A²s
dl _T /dt	rate of rise of on-state current	I _G = 100 mA	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C

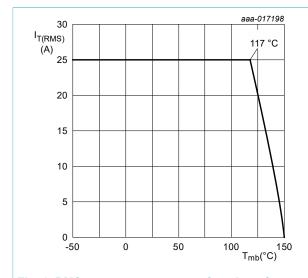


Fig. 1. RMS on-state current as a function of mounting base temperature

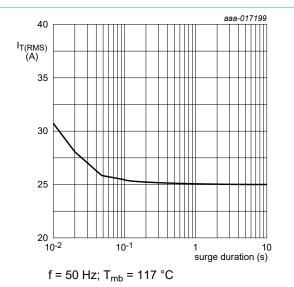


Fig. 2. RMS on-state current as a function of surge duration; maximum values

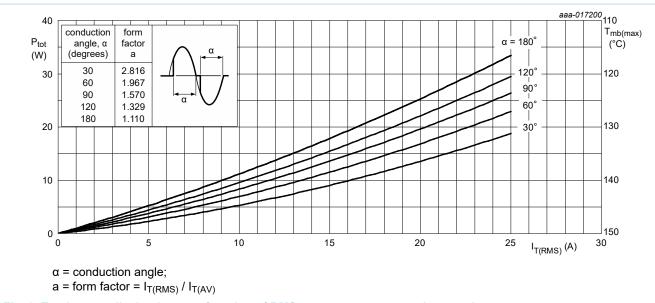


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

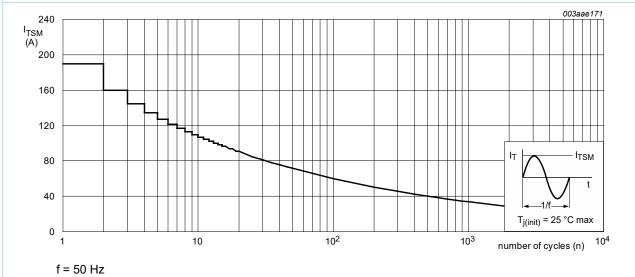
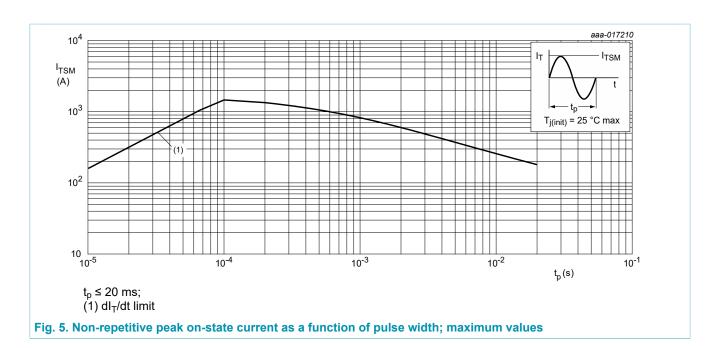


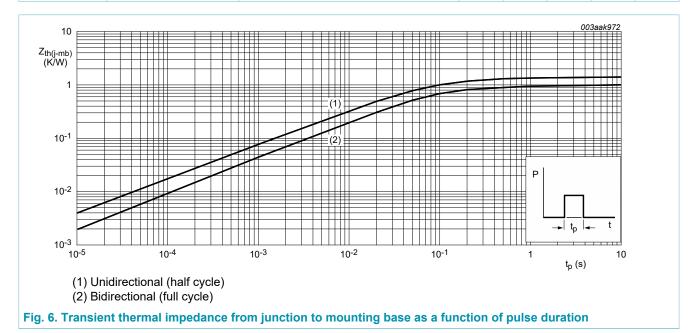
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	1	K/W
		half cycle; Fig. 6	-	-	1.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	55	-	K/W



9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,			
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	2	18	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	2	21	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	2	34	50	mA
L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	31	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	34	90	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	30	60	mA
Н	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	31	60	mA
/ _T	on-state voltage	I _T = 30 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.55	V
V _{GT}	gate trigger voltage	V _D = 400 V; I _T = 0.1 A; T _j = 150 °C	-	0.6	-	V
		V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
D	off-state current	V _D = 800 V; T _j = 150 °C	-	8.0	4	mA
		V _D = 800 V; T _j = 25 °C	-	0.1	10	μΑ
		V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	-	2300	-	V/µs
		V _{DM} = 536 V; T _j = 125 °C; exponential waveform; gate open circuit	1000	4000	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 25 A; dV_{com}/dt = 20 V/µs; (without snubber condition); gate open circuit	-	19	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 25 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s}; (snubber condition); gate open circuit$	-	44	-	A/ms

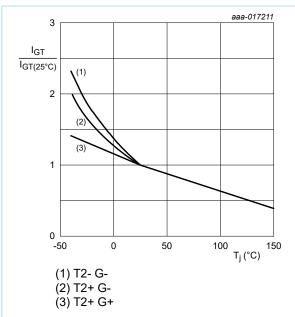


Fig. 7. Normalized gate trigger current as a function of junction temperature

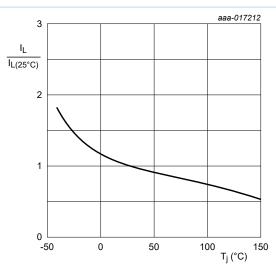


Fig. 8. Normalized latching current as a function of junction temperature

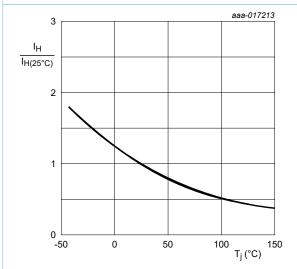
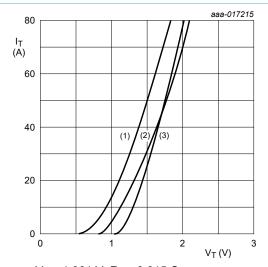


Fig. 9. Normalized holding current as a function of junction temperature

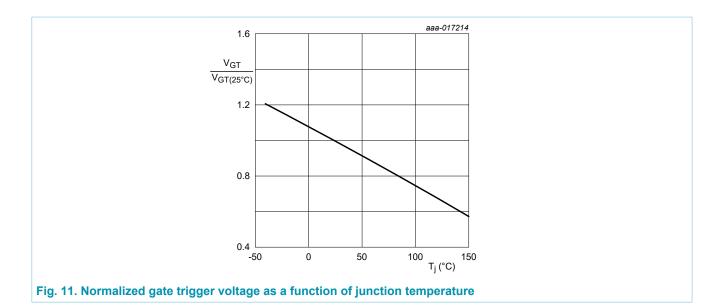


 V_o = 1.061 V; R_s = 0.015 Ω

(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

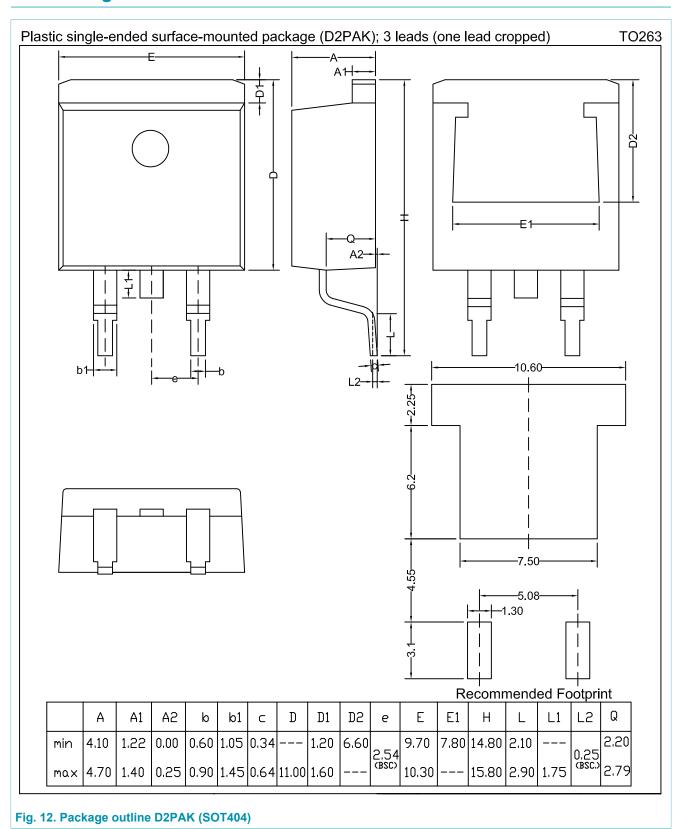
(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage



BTA225B-800BT

10. Package outline



11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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For more information, please visit: http://www.ween-semi.com
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